TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 1 (PRIOR ART)

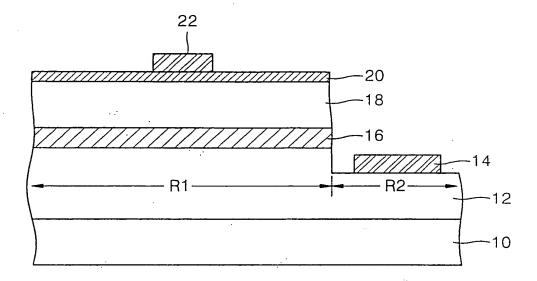
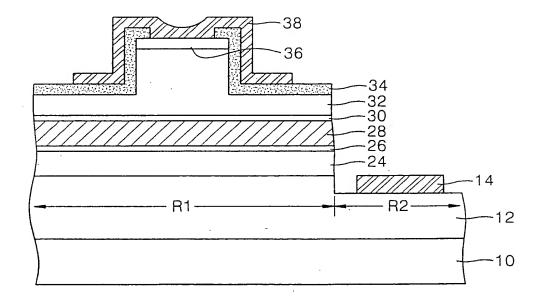


FIG. 2 (PRIOR ART)



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 3 (PRIOR ART)

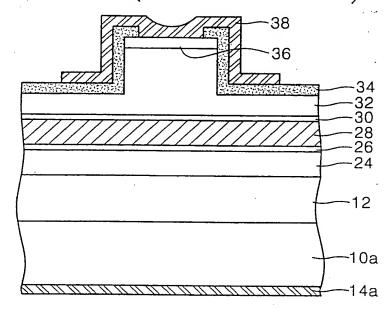
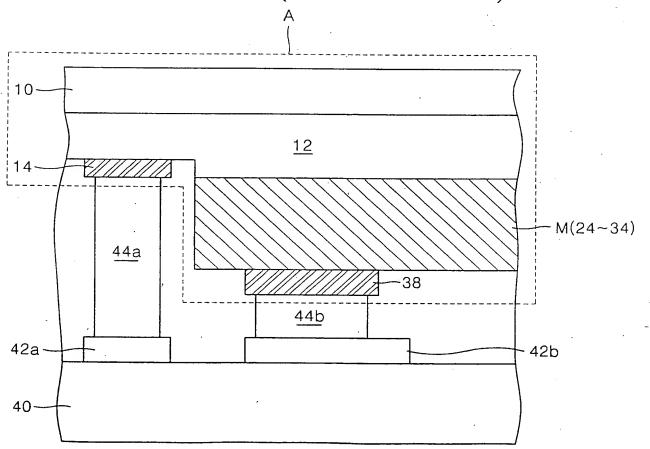


FIG. 4 (PRIOR ART)



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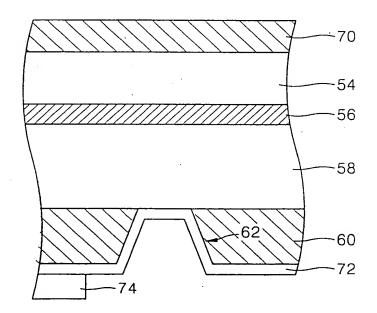
SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 5 52 54 -56 -58 62 60 -64

FIG. 6



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FIG. 7

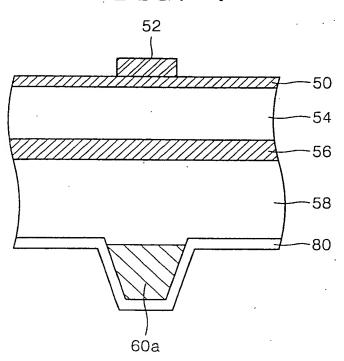
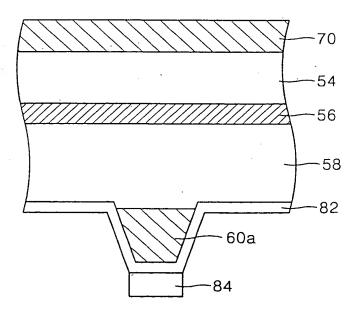


FIG. 8



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SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG.

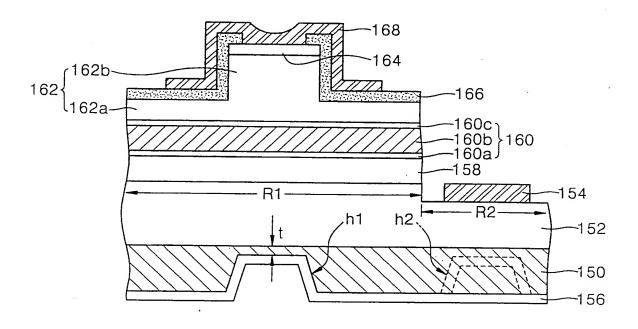
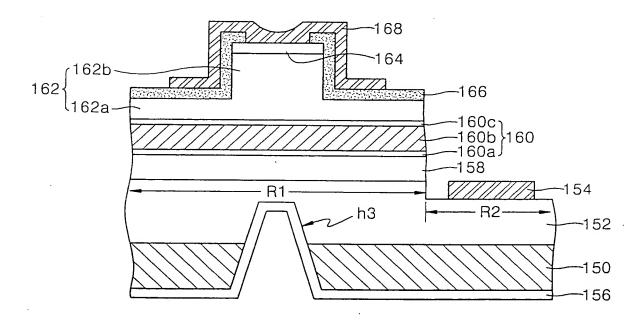


FIG. 10



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 11

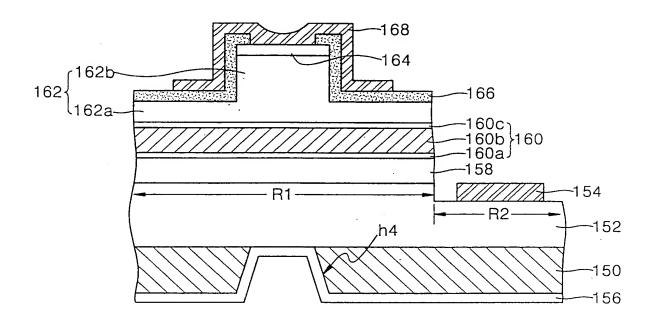
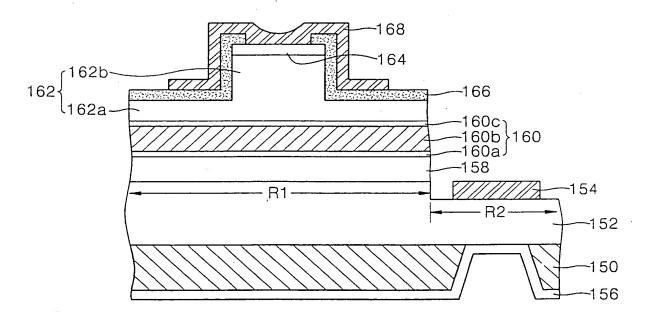


FIG. 12



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 13

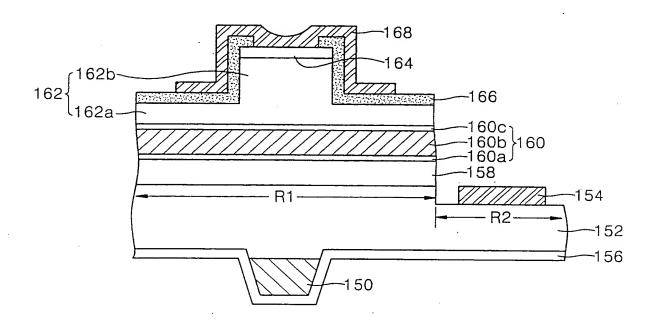
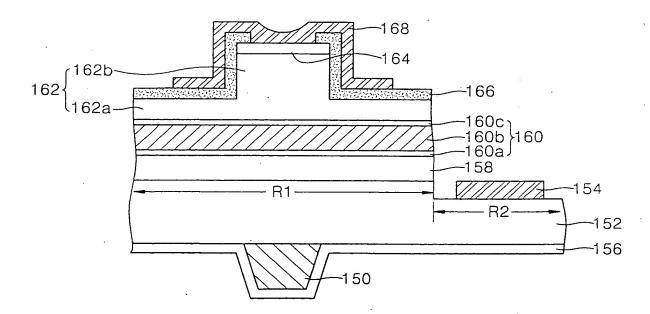


FIG. 14



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 15

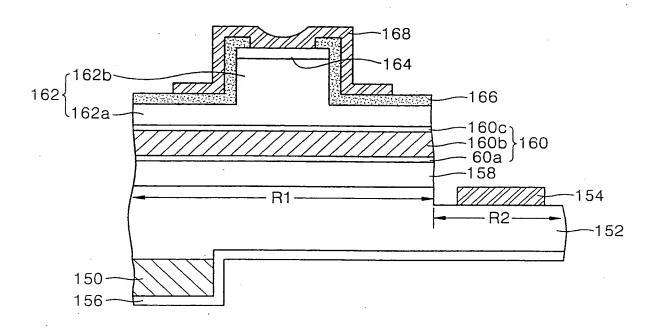
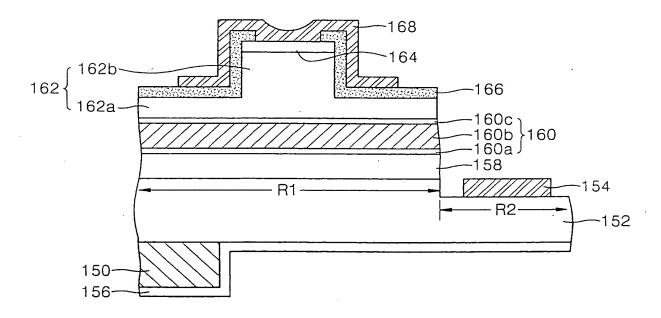


FIG. 16



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 17

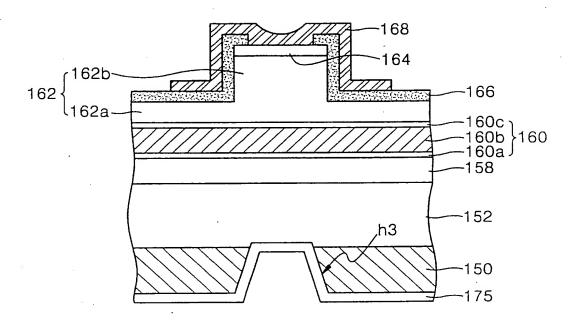
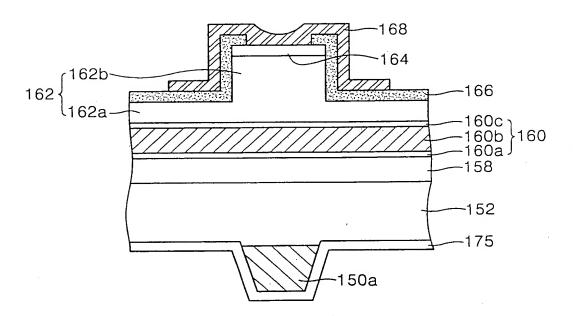


FIG. 18



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 19

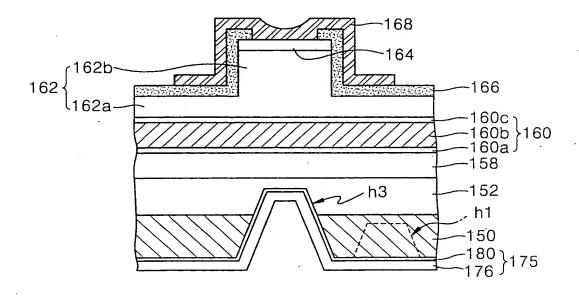
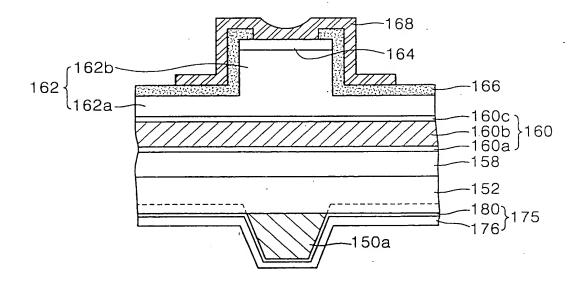


FIG. 20



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

INVENTOR(S): JOON-SEOP KWAK ET AL

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FIG. 21

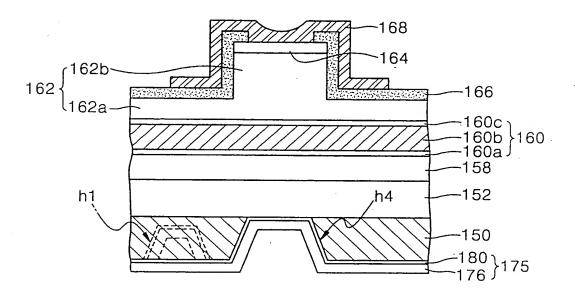
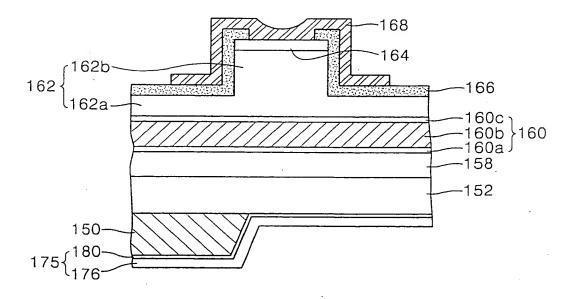


FIG. 22



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL

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FIG. 23

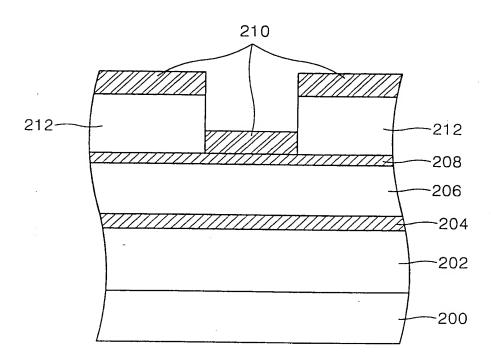
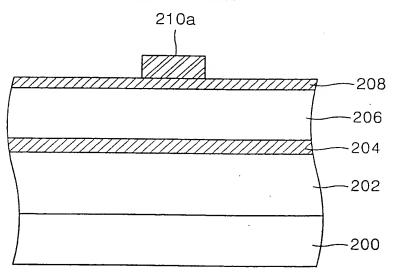


FIG. 24



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 25

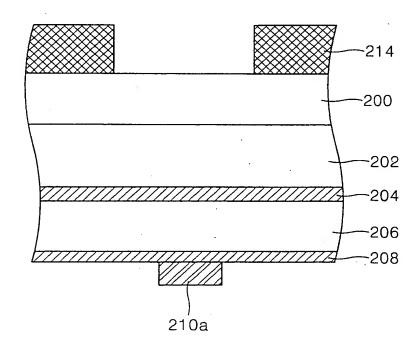
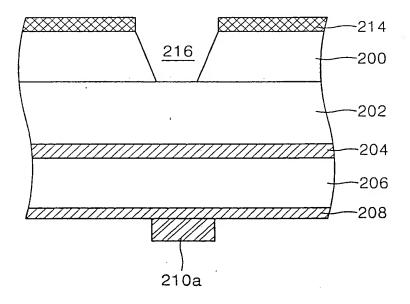


FIG. 26



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 27

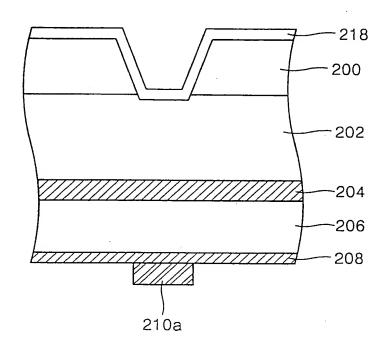
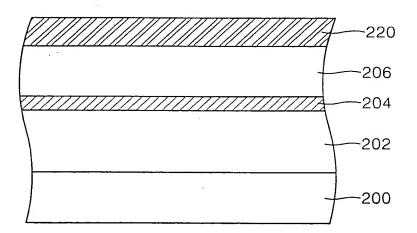


FIG. 28



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 29

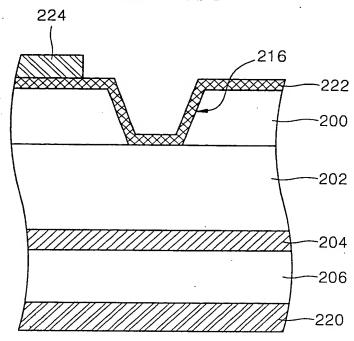
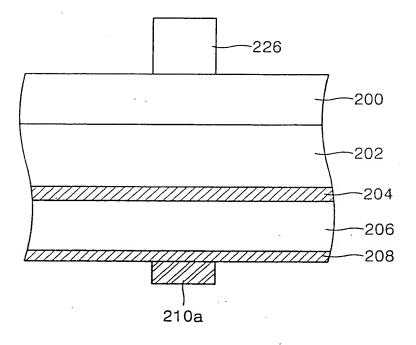


FIG. 30



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SAME

INVENTOR(S): JOON-SEOP KWAK ET AL

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FIG. 31

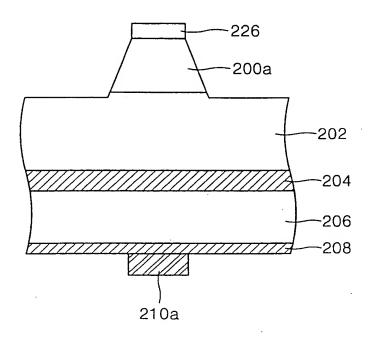
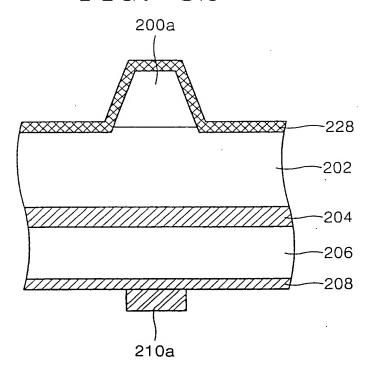


FIG. 32



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INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 33

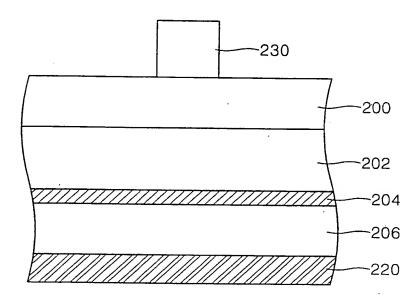
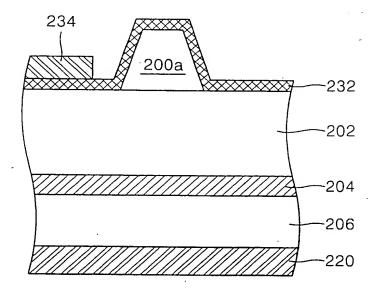


FIG. 34



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL

ATTORNEY'S DOCKET NO: 030681-576

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FIG. 35

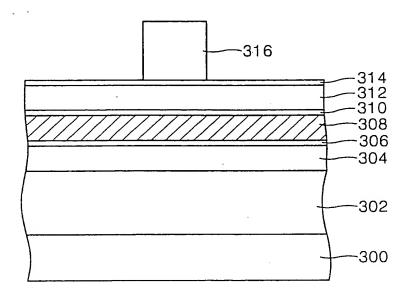
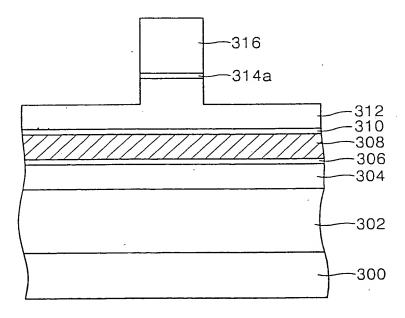


FIG. 36



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE

SAME

INVENTOR(S): JOON-SEOP KWAK ET AL

ATTORNEY'S DOCKET No: 030681-576

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FIG. 37

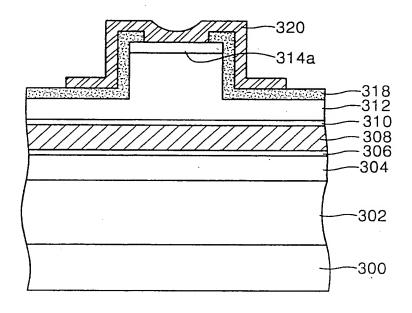
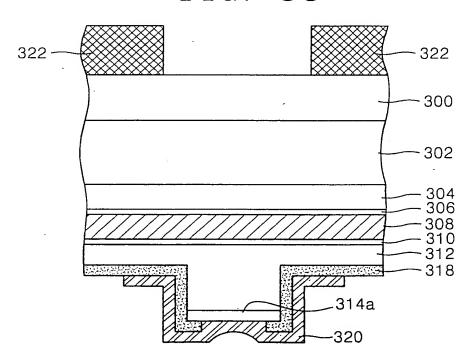


FIG. 38



TITLE: GAN BASED GROUP III-V NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE AND METHOD FOR FABRICATING THE SAME

INVENTOR(S): JOON-SEOP KWAK ET AL

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FIG. 39

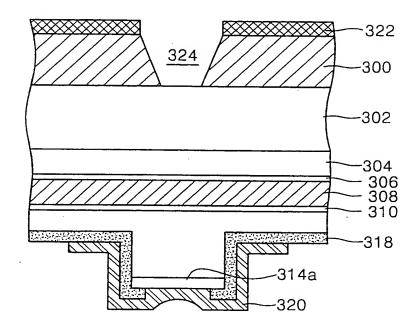
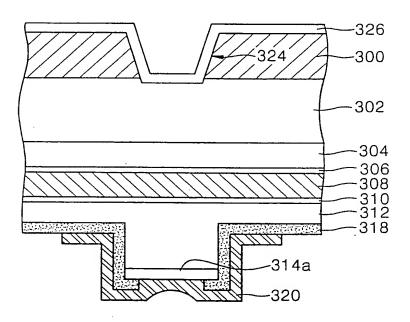


FIG. 40



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SAME INVENTOR(S): JOON-SEOP KWAK ET AL ATTORNEY'S DOCKET NO: 030681-576

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FIG. 41

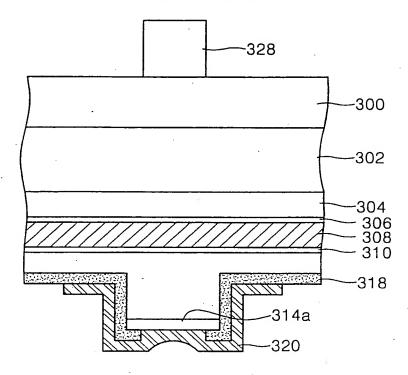
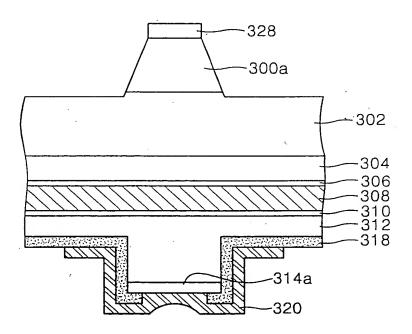


FIG. 42



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INVENTOR(S): JOON-SEOP KWAK ET AL

ATTORNEY'S DOCKET NO: 030681-576 **SHEET 22 of 22**

FIG. 43

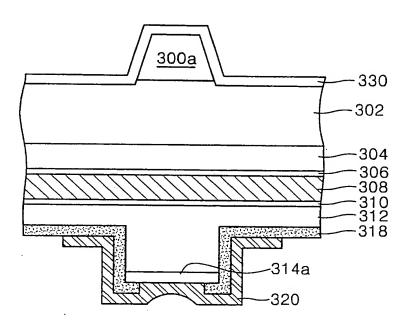


FIG. 44

